

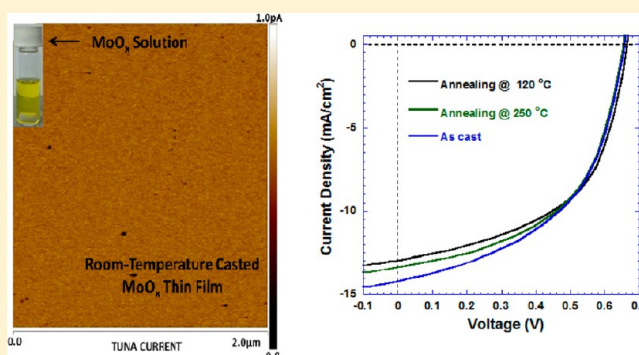
# Room-Temperature, Solution-Processed MoO<sub>x</sub> Thin Film as a Hole Extraction Layer to Substitute PEDOT/PSS in Polymer Solar Cells

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**ABSTRACT:** Room-temperature, solution-processed molybdenum oxide (MoO<sub>x</sub>) as a hole extraction layer to substitute PEDOT/PSS in polymer solar cells was demonstrated. The thin film of MoO<sub>x</sub> shows a smoother surface, better transparency, and high electrical conductivity than that of PEDOT/PSS thin layer and, thus, leading enhanced efficiency of PSCs than those using PEDOT/PSS anode buffer layer. These results demonstrated that the utilization of room-temperature, solution-processed MoO<sub>x</sub> thin film as a hole extraction layer in polymer solar cells blaze a trail to achieve high performance devices.

**KEYWORDS:** polymer solar cells, hole extracting buffer layer, room-temperature processing, efficiency, stability, PEDOT/PSS replacement



In the past two decades, bulk heterojunction (BHJ) polymer solar cells (PSCs) have been attracting intense attention due to their advantages over traditional inorganic solar cells such as flexibility, low-cost, lightweight, large area, clean and quiet, and processing simplicity.<sup>1,2</sup> In PSCs, BHJ composite is sandwiched between a poly(3,4-ethylenedioxythiophene) poly(styrenesulfonate) (PEDOT/PSS) coated indium tin oxide (ITO) anode and a low-work-function cathode, for example, calcium (Ca) or aluminum (Al); however, the acidic PEDOT/PSS etches ITO and causes PSCs degradation.<sup>3,4</sup> One possible solution to overcome these problems is to substitute PEDOT/PSS layer by using a stable metal oxide layer with suitable energy level alignment between the ITO anode and BHJ active layer.<sup>5,6</sup>

Many metal oxides have been utilized as a hole extraction layer (HEL) in PSCs;<sup>7–9</sup> but the improvements in efficiency are still not sufficient. Molybdenum oxide is among all such metal oxide candidates and has been extensively studied for its transparency in visible range, good stability, and hole mobility.<sup>10,11</sup> The efficiencies of PSCs incorporating with vacuum-deposited metal oxides as a HEL were compatible to those using PEDOT/PSS as an anode buffer layer,<sup>12</sup> whereas the efficiencies of PSCs incorporating with solution-processed metal oxides were lower than those using PEDOT/PSS.<sup>5,13,14</sup> This is because the major challenges in widely used precursor methods for formation of metal oxide thin film with good hole transport properties usually require a thermal annealing at elevated temperature. Unfortunately, many plastic substrates that are used for fabricating polymer solar cells cannot sustain elevated annealing temperature due to subsequently reduced optical transparency and thermal and dimensional stability at high temperature.<sup>15,16</sup> In addition, high-temperature annealing

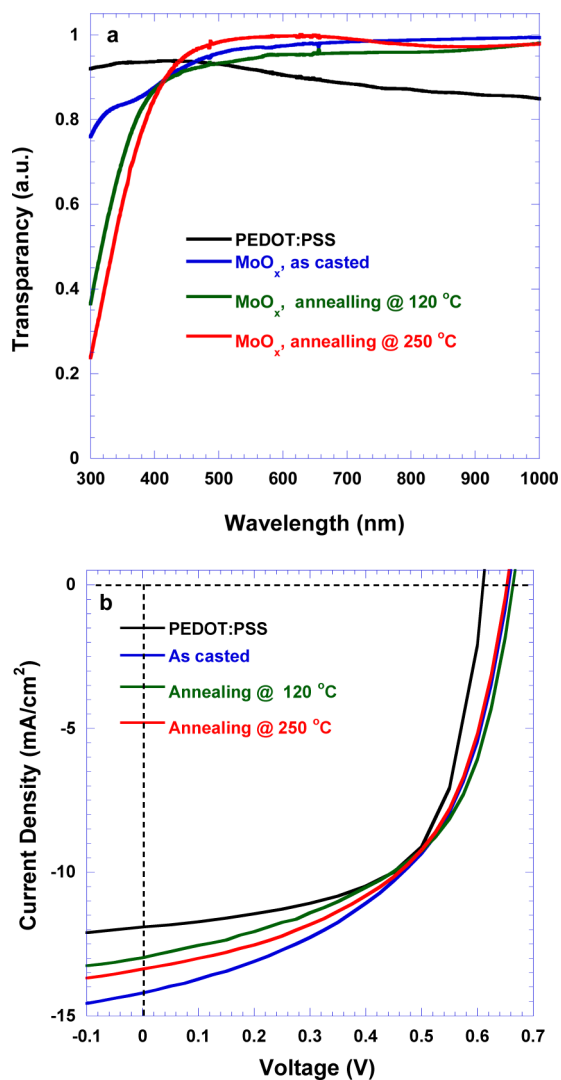
large-area metal oxides is converse to the low-cost manufacturing PSCs. In answering the need for fabricating low-temperature, solution-processed PSCs with improved performance at low cost, a new method for processing metal oxides with thermal treatment at low temperature shall be realized and utilized.

In our previous work, we reported compatible efficiencies from PSCs with MoO<sub>x</sub> thin film as a HEL compared to those using PEDOT/PSS as an anode buffer layer, where the sol-gel-derived MoO<sub>x</sub> thin film has to be thermally annealed at 250 °C to ensure it has proper hole transporting properties.<sup>10</sup> In this paper, a water-free, room-temperature solution-processed MoO<sub>x</sub> thin film as a HEL in PSCs was demonstrated. Such low-temperature processing will broaden the selection of substrates in future large scale PSC module production on plastic substrates, where processing temperature is a critical consideration.

The MoO<sub>x</sub> thin film was spin-casted from MoO<sub>x</sub> methanol solution which was prepared as follows: with vigorous stirring and effective radiating, 100 mL of H<sub>2</sub>O<sub>2</sub> (concentration of 30%) was slowly added into 10 g molybdenum powder (CAS #7439–98–7, Alfa Aesar, Stock #00932, Lot #L13X018) in a clean beaker that sits in an ice–water bath to aid the radiating process. The obtained solution is then centrifuged to remove the rudimental substance. Clear solution is subsequently subjected to distillation to remove the solvent, H<sub>2</sub>O and give dry MoO<sub>x</sub> powder. Dried MoO<sub>x</sub> powder is dissolved in methanol for the preparation of MoO<sub>x</sub> thin film.

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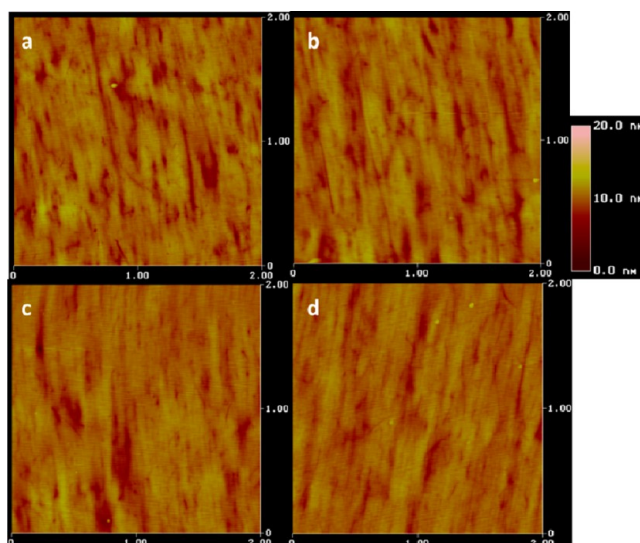
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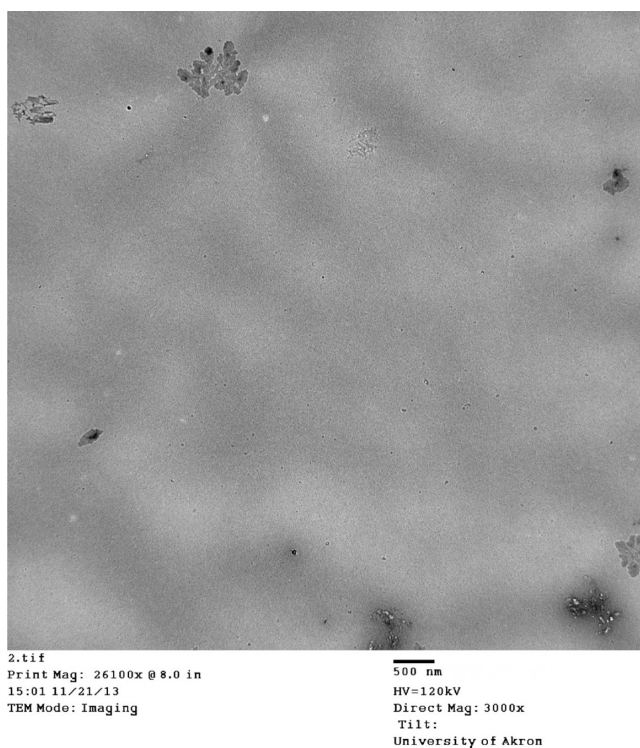
**Figure 1.** (a) Transparency spectra of MoO<sub>x</sub> thin film annealed at different temperatures and PEDOT/PSS thin film; (b) Current-density versus voltage characterization of polymer solar cells using different anode buffer layers.

The transmission spectra of MoO<sub>x</sub> thin films treated at different temperatures are shown in Figure 1a. The transmission spectrum of PEDOT/PSS thin layer is also presented in Figure 1a for comparison. A high transmittance in the visible range is desired when MoO<sub>x</sub> thin film is expected to be a HEL inserted between the ITO anode and the BHJ composite layer. Greater than 90% transparency ranging from 500 to 1000 nm is observed from MoO<sub>x</sub> thin films treated at different temperatures. The weak absorption from 800 to 900 nm is attributed to the free electrons being trapped by oxygen vacancies in MoO<sub>x</sub> thin films.<sup>17</sup> Nevertheless, the transmittance of MoO<sub>x</sub> thin films is higher than that of the PEDOT/PSS layer, indicating that MoO<sub>x</sub> thin film is qualified to be a HEL through which more visible light is able to transmit from the ITO/MoO<sub>x</sub> into the BHJ active layer without significant absorption losses.

The effect of MoO<sub>x</sub> thin films on the device performance of PSCs was investigated using a device configuration of ITO/MoO<sub>x</sub>/PTB7-F20:PC<sub>71</sub>BM/Ca/Al and compared with the device performance from PSCs using PEDOT/PSS as an anode buffer layer. PTB7-F20 was novel narrow bandgap

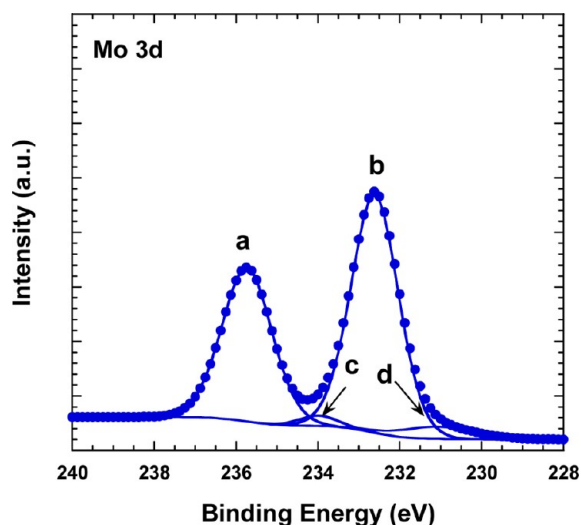


**Figure 2.** AFM images of bare ITO and MoO<sub>x</sub> thin films: (a) bare ITO (RMS = 1.454 nm), (b) MoO<sub>x</sub> as casted (RMS = 1.272 nm), (c) MoO<sub>x</sub> thermal annealing at 120 °C (RMS = 1.637 nm), and MoO<sub>x</sub> thermal annealing at 250 °C (RMS = 1.009 nm).



**Figure 3.** Imaging TEM result of MoO<sub>x</sub> thin film spin-casted from 10 mg/mL methanol solution.

conjugated polymer and was reported elsewhere.<sup>18</sup> The  $J$ - $V$  curves of PSCs are shown in Figure 1b. Under AM1.5G illumination with the light intensity of 100 mW cm<sup>-2</sup>, an open-circuit voltage ( $V_{OC}$ ) of 0.60 V, a short-circuit current density ( $J_{SC}$ ) of 11.92 mAcm<sup>-2</sup>, a fill factor (FF) of 62%, and a corresponding PCE of 4.43% were obtained from PSCs by using PEDOT/PSS as an anode buffer layer. At the same condition, a  $V_{OC}$  of 0.65 V, a  $J_{SC}$  of 14.2 mA cm<sup>-2</sup>, a FF of 50.7%, and a corresponding PCE of 4.67% were observed from PSCs by using MoO<sub>x</sub> thin film without any treatment as a HEL.



**Figure 4.** XPS spectra of Mo 3d core level from MoO<sub>x</sub> thin film processed in room-temperature: major peaks, (a) Mo<sup>6+</sup> (235.8 eV), (b) Mo<sup>6+</sup> (235.8 eV); minor peaks, (c) Mo<sup>5+</sup> (234.0 eV), (d) Mo<sup>5+</sup> (231.1 eV).

For PSCs by using MoO<sub>x</sub> thin film, which is annealed at 120 °C as a HEL, a  $V_{OC}$  of 0.67 V, a  $J_{SC}$  of 13.0 mA cm<sup>-2</sup>, a FF of 52.8%, and a corresponding PCE of 4.62% were observed. For PSCs by using MoO<sub>x</sub> thin film, which is annealed at 250 °C as a HEL, a  $V_{OC}$  of 0.65 V, a  $J_{SC}$  of 12.4 mA cm<sup>-2</sup>, a FF of 53.2%, and a corresponding PCE of 4.63% were observed. Among these PSCs, PSCs with as casted MoO<sub>x</sub> thin film as a HEL gave the best device performance.

In order to understand underlying device performance, we investigated surface morphology of MoO<sub>x</sub> thin films by atomic force microscopy (AFM). Tapping mode AFM images of MoO<sub>x</sub> thin films with different annealing conditions are shown in Figure 2. MoO<sub>x</sub> thin films were spin-casted on pre-cleaned ITO substrates. The root-mean-square (RMS) roughness of MoO<sub>x</sub> thin film without any treatment is 1.272 nm, which is smaller than those from bare ITO (1.454 nm) and MoO<sub>x</sub> thin film annealed at 120 °C (1.637 nm); however, it is larger than that from MoO<sub>x</sub> thin film annealed at 120 °C (1.099 nm). The smooth surface implies that the BHJ composite layer can be easily deposited onto the top of MoO<sub>x</sub> thin layer; consequently, PSCs with high efficiency is expected.

MoO<sub>x</sub> thin film quality is investigated by using transmission electron microscopy (TEM). MoO<sub>x</sub> thin films were spin-casted on carbon-coated copper grids from a high MoO<sub>x</sub> concentration solution of 10 mg/mL in methanol. The obtained samples were dried in vacuum for 30 min before conducting the TEM study. The obtained TEM image is shown in Figure 3. It was found out that the MoO<sub>x</sub> thin film shows a good uniformity. This result is attributed to the good solubility of the synthesized MoO<sub>x</sub> powered in methanol, which will lead to the

formation of a homogeneous solution for subsequent spin coating of a fine MoO<sub>x</sub> thin film.

We further studied the stoichiometric composition of MoO<sub>x</sub> thin films by X-ray photoelectron spectroscopy (XPS). Figure 4 presents XPS spectra of MoO<sub>x</sub> thin film without any treatment. Decomposition of the XPS spectrum reveals two 3d doublets, which are corresponding to two different oxidation states, in the form of a Gaussian function for the Mo 3d spectrum. It is shown that the major peak appears at the binding energy of 232.6 and 235.8 eV are corresponded to 3d doublet of Mo<sup>6+</sup>.<sup>14</sup> The minor peak is centered at 234 and 231.1 eV, which are typical values of 3d doublet of Mo<sup>5+</sup>.<sup>19</sup> The molybdenum to oxygen stoichiometry data obtained from the XPS spectra of MoO<sub>x</sub> thin films are summarized in Table 1. It revealed that the ratio of molybdenum to oxygen increases along with increased annealing temperatures, resulting in oxygen deficiency in MoO<sub>x</sub> thin films at high annealing temperature.<sup>20</sup> Thus, the samples exhibit a more ideal MoO<sub>3</sub> lattice stoichiometry when annealed at lower temperatures, leading to a minimized Mo<sup>5+</sup> and oxygen deficiency. The atomic concentration ratio of Mo<sup>5+</sup> to Mo<sup>6+</sup> obtained from room-temperature, processed MoO<sub>x</sub> films is around 1:3.38, which indicates a less oxygen vacancies in MoO<sub>x</sub>, resulting in high electrical conductivity. Because device performance is reversely related to the density of Mo<sup>5+</sup> species in MoO<sub>x</sub> thin films (with decreased Mo<sup>5+</sup> and oxygen deficiency, the resulting device will have better performance),<sup>20</sup> room-temperature, processed MoO<sub>x</sub> thin film will contribute to an increase in device performance.

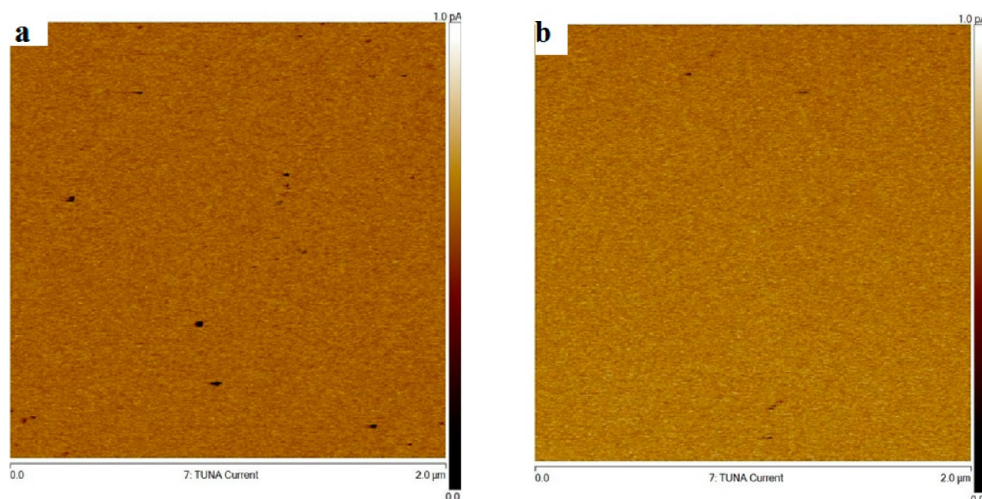
We further measured the surface electrical conductivities of MoO<sub>x</sub> thin films by peak force tapping tunneling AFM (PF-TUNA) module.<sup>10,21</sup> The probe was the PF-TUNA probe with spring constant of ~0.5 N m<sup>-1</sup> with 20 nm Pt/Ir coating on both front and rear. The spring currents were measured with bias voltage applied to the sample. The ramp rate of 0.4 Hz and the force set point of ~60 nN were used for both thin films. The peak currents of MoO<sub>x</sub> thin films without thermal annealing and with thermal annealing at 250 °C are shown in Figure 5. The surface electrical conductivity of MoO<sub>x</sub> thin films with thermal annealing at 250 °C and without thermal annealing are 0.601 and 0.642 pA, respectively. Thus, surface electrical conductivity of MoO<sub>x</sub> thin film without any thermal annealing is higher than that of MoO<sub>x</sub> thin films with thermal annealing at 250 °C. As a result, the efficiency from PSCs using MoO<sub>x</sub> thin film without any thermal annealing as a HEL is higher than that using MoO<sub>x</sub> thin films with thermal annealing at 250 °C.

In conclusion, room-temperature, solution-processed MoO<sub>x</sub> thin film as a hole extraction layer to substitute PEDOT/PSS in polymer solar cells was demonstrated. The thin film of MoO<sub>x</sub> shows a smoother surface, better transparency and high electrical conductivity than that of PEDOT/PSS thin layer and thus leading enhanced efficiency of PSCs than those using PEDOT/PSS anode buffer layer. These results demonstrated that the utilization of room-temperature, solution-processed

**Table 1.** XPS Compositional Analysis of Solution-Processed MoO<sub>x</sub> Thin Films

	MoO <sub>x</sub> as spin-casted	MoO <sub>x</sub> annealing @ 120 °C	MoO <sub>x</sub> annealing @ 250 °C
molybdenum	15.1	20.8	22.0
oxygen	51.1	55.7	52.4
carbon	33.8	23.5	25.6
Mo/O ratio	1:3.38	1:2.67	1:2.38





**Figure 5.** Peak current of MoO<sub>x</sub> thin films: (a) without any treatment; (b) annealing at 250 °C.

MoO<sub>x</sub> thin film as a hole extraction layer in polymer solar cells blaze a trail to achieve high performance devices.

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### Notes

The authors declare no competing financial interest.

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